

isc N-Channel MOSFET Transistor

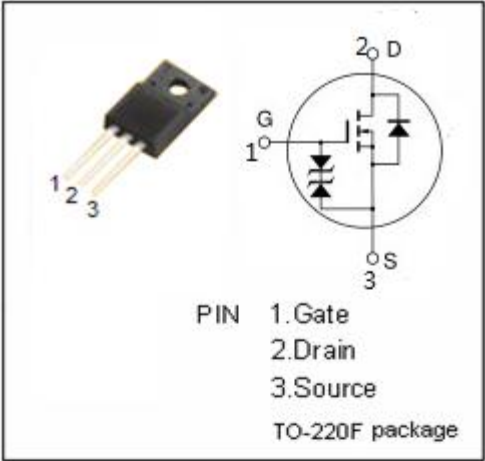
2SK2236

DESCRIPTION

- Drain Current $-I_D= 5A @ T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}= 500V(Min)$
- Fast Switching Speed

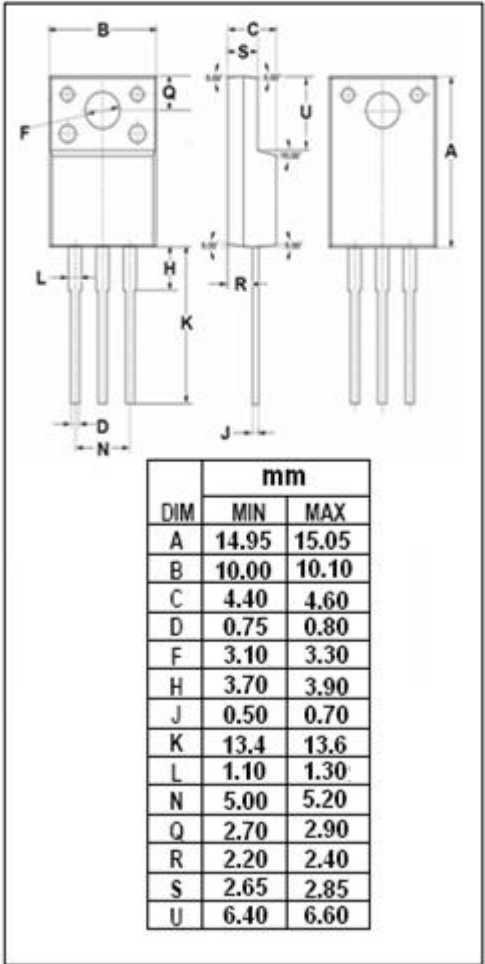
APPLICATIONS

- Switching regulators ,DC-DC converter, Motor Control



ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS}=0$)	500	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-continuous@ $TC=25^{\circ}C$	5	A
$I_{D(puls)}$	Pulsed Drain Current	20	A
P_{tot}	Total Dissipation@ $TC=25^{\circ}C$	40	W
T_j	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}C$



isc N-Channel Mosfet Transistor**2SK2236**• ELECTRICAL CHARACTERISTICS ($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=10\text{mA}$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10\text{V}$; $I_D=1\text{mA}$	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}$; $I_D=2.5\text{A}$			1.6	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}$; $V_{DS}=0$			± 100	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=500\text{V}$; $V_{GS}=0$			500	μA